

AP3967

General Description

The AP3967 consists of a primary side regulation controller and a high voltage transistor, and is specially designed for off-line power supplies within 3.5W output power. Typical applications include adapter for ADSL and auxiliary supplies.

The AP3967 operates at pulse frequency modulation (PFM), and provides accurate constant voltage, constant current (CV/CC) regulation without requiring an opto-coupler and secondary control circuitry. It has internal cable compensation function for tight constant voltage regulation.

The AP3967 solution has fewer component numbers, smaller size, and lower total cost.

The AP3967 is packaged in SOIC-7.

Features

- Primary Side Control for Eliminating Opto-coupler and Secondary CV/CC Control Circuitry
- Built-in NPN Transistor with $700V_{CBO}$
- Low Start-up Current: 0.2μA (Typ.)
- Internal Output Cable Voltage Drop Compensation
- Random Frequency Modulation for Low EMI
- Short Circuit Protection
- Low Total Cost Solution
- Output Power Range: For 3.5W Adapter

Applications

- Chargers
- Adapters
- Set Top Boxes
- · Auxiliary Supplies
- DVD
- LED Driver

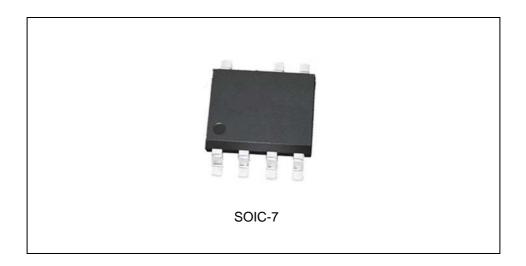


Figure 1. Package Type of AP3967



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Pin Configuration

M Package (SOIC-7)

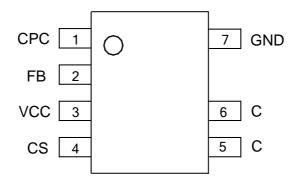


Figure 2. Pin Configuration of AP3967 (Top View)

Pin Description

Pin Number	Pin Name	Function		
1	CPC	This pin connects a capacitor to GND for output cable compensation		
2	FB	The voltage feedback from auxiliary winding		
3	VCC	This pin receives rectified voltage from the auxiliary winding of the transformer		
4	CS	Current sense for primary side of transformer		
5, 6	С	This pin is connected with an internal power BJT's collector		
7	GND	This pin is the signal reference ground		



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Functional Block Diagram

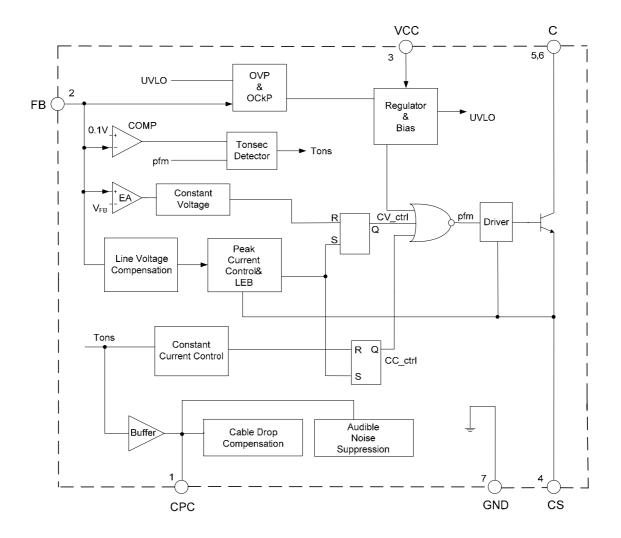
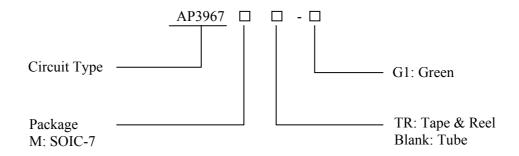


Figure 3. Functional Block Diagram of AP3967



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Ordering Information



Package	Temperature Range	Part Number	Marking ID	Packing Type	
SOIC-7	-40 to 85°C	AP3967M-G1	3967M-G1	Tube	
		AP3967MTR-G1	3967M-G1	Tape & Reel	

BCD Semiconductor's Pb-free products, as designated with "G1" suffix in the part number, are RoHS compliant and green.



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Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit	
Supply Voltage	V_{CC}	-0.3 to 22	V	
FB Input Voltage	V_{FB}	-1 to 10	V	
Collector-emitter Voltage	V_{CBO}	700	V	
Collector DC Current		0.8	A	
Operating Junction Temperature	T_{J}	150	°C	
Storage Temperature	T_{STG}	-65 to 150	°C	
Lead Temperature (Soldering, 10 sec)	T_{LEAD}	300	°C	
ESD (Machine Model)		200	V	
ESD (Human Body Model)		2000	V	

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}		22	V
Operating Temperature Range	T_{OP}	-40	85	°C
Maximum Operating Frequency	f_{MAX}		60	kHz



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Electrical Characteristics

V_{CC}=15V, T_J=25°C, unless otherwise specified.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
UVLO Section							
Turn-on Voltage	V_{ON}		13	15	17	V	
Turn-off Voltage	V _{OFF}	No drive Current	4.5	5.3	6.3	V	
Standby Current Section							
Start-up Current	I_{ST}	V _{CC} =V _{ON} -0.5V		0.2	0.6		
Operating Current	I_{CC}		320	435	550	μΑ	
Feedback Input Section					•		
FB Input Current	I_{FB}	V _{FB} =4V	1.5	3.5	5.5	μΑ	
FB Threshold Voltage	V_{FB}		4.214	4.278	4.342	V	
Power Transistor Section					•		
Collector-emitter Saturation Voltage	V _{CE(SAT)}	I _C =200mA			0.3	V	
DC Current Gain	h_{FE}		15	23			
Leakage Current	I _{CEO}				60	nA	
Over Temperature Protect	ion	•	•		•		
Shutdown Temperature	T_{SHDN}	Surface temperature	125	160		°C	
Temperature Hysteresis				40		°C	

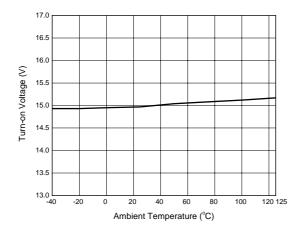
Thermal Impedance

Parameter	Symbol	Value	Unit	
Junction to Ambient	$ heta_{ m JA}$	80		
Junction to Case	$\theta_{ m JC}$	40	°C/W	



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Typical Performance Characteristics



6.5 6.0 (S) 5.5 4.5 4.0 3.5 3.0 -40 -20 0 20 40 60 80 100 120 125 Ambient Temperature (°C)

Figure 4. Turn-on Voltage vs. Ambient Temperature

Figure 5. Turn-off Voltage vs. Ambient Temperature

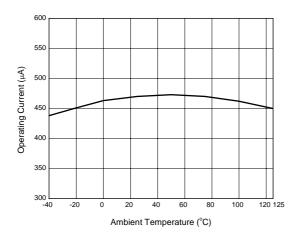


Figure 6. Operating Current vs. Ambient Temperature

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Operation Description

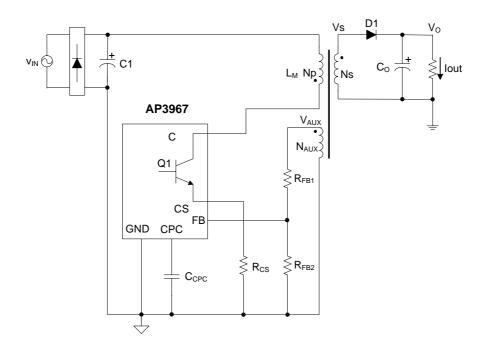


Figure 7. Simplified Flyback Converter Controlled by AP3967

Figure 7 illustrates a simplified flyback converter controlled by AP3967.

Constant Primary Peak Current

The primary current Ip(t) is sensed by a current sense resistor R_{CS} as shown in Figure 7.

The current rises up linearly at a rate of:

$$\frac{dip(t)}{dt} = \frac{vg(t)}{L_{M}}....(1)$$
See equation 2

Figure 8. Primary Current Waveform

As illustrated in Figure 8, when the current Ip(t) rises up to Ipk, the switch Q1 turns off. The constant peak current is given by:

$$Ipk = \frac{Vcs}{Rcs} \dots (2)$$

The energy stored in the magnetizing inductance L_{M} each cycle is therefore:

$$Eg = \frac{1}{2} \cdot L_{M} \cdot Ipk^{2} \cdot \dots (3)$$

So the power transferring from input to output is given by:

$$P = \frac{1}{2} \cdot L_{M} \cdot Ipk^{2} \cdot f_{SW} \cdot \dots (4)$$

Where f_{SW} is the switching frequency. When the peak current Ipk is constant, the output power depends on the switching frequency f_{SW} .

Constant Voltage Operation

The AP3967 captures the auxiliary winding feedback voltage at FB pin and operates in constant-voltage (CV) mode to regulate the output voltage. Assuming



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the secondary winding is master, the auxiliary winding is slave during the D1 on-time. The auxiliary voltage is given by:

$$V_{AUX} = \frac{N_{AUX}}{N_S} \cdot (V_0 + V_d) \cdot \dots (5)$$

Where V_d is the diode forward drop voltage, N_{AUX} is the turns of auxiliary winding, and N_S is the turns of secondary winding.

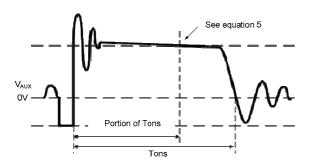


Figure 9. Auxiliary Voltage Waveform

The output voltage is different from the secondary voltage in a diode forward drop voltage V_d which depends on the current. If the secondary voltage is always detected at a constant secondary current, the difference between the output voltage and the secondary voltage will be a fixed V_d . The voltage detection point is portion of Tons after D1 is turned on. The CV loop control function of AP3967 then generates a D1 off-time to regulate the output voltage.

Constant Current Operation

The AP3967 is designed to work in constant current (CC) mode. Figure 10 shows the secondary current waveforms.

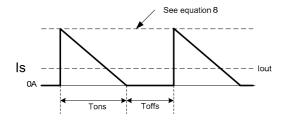


Figure 10. Secondary Current Waveform

In CC operation, the CC loop control function of AP3967 will keep a fixed proportion between D1 on-time Tons and D1 off-time Toffs by discharging or

charging the built-in capacitance connected. This fixed proportion is:

$$\frac{\text{Tons}}{\text{Toffs}} = \frac{4}{3} \dots (6)$$

The relation between the output constant-current and secondary peak current Ipks is given by:

$$Iout = \frac{1}{2} \cdot Ipks \cdot \frac{Tons}{Tons + Toffs} \dots (7)$$

At the instant of D1 turn-on, the primary current transfers to the secondary at an amplitude of:

$$Ipks = \frac{N_p}{N_s} \cdot Ipk \dots (8)$$

Thus the output constant current is given by:

$$Iout = \frac{2}{7} \cdot \frac{N_p}{N_s} \cdot Ipk \dots (9)$$

Leading Edge Blanking (LEB)

When the power switch is turned on, a turn-on spike on the output pulse rising edge will occur on the sense-resistor. To avoid false termination of the switching pulse, a typical 500ns leading edge blanking is built in. During this blanking period, the current sense comparator is disabled and the gate driver can not be switched off.

The built-in LEB in AP3967 has shorter delay time from current sense terminal to output pulse than those IC solutions adopting external RC filter as LEB.

Built-in Cable Compensation

The AP3967 has built-in fixed voltage of 0.35V typical to compensate the drop of output cable when the load is changed from zero to full load. A typical $0.01\mu F$ external capacitor connected to the CPC pin is used to smooth voltage signal for cable compensation.

Over Temperature Protection

The AP3967 has internal thermal sensing circuit to shut down the PFM driver output when the die temperature reaches 160°C typical. When the die temperature drops about 40°C, the IC will recover automatically to normal operation.



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Typical Application

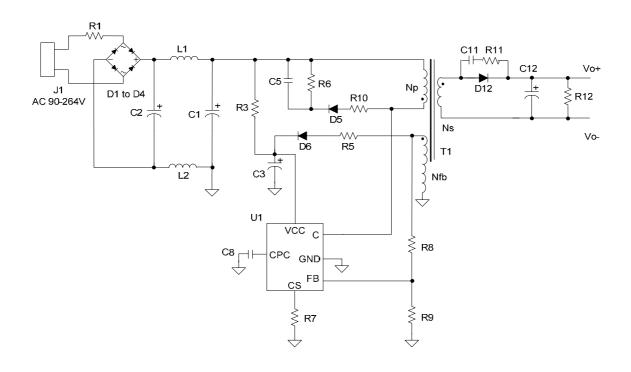


Figure 11. Typical Application of AP3967 (5V/700mA)

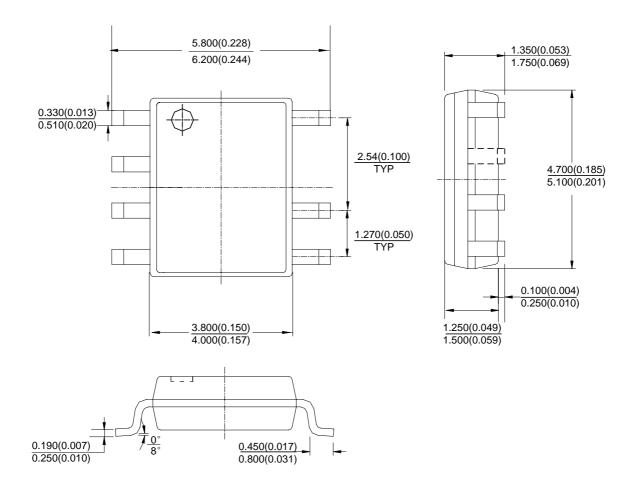
Item	Description	QTY	Item	Description	QTY
C1	10.0μF/400V, electrolytic	1	R1	11Ω, 2W	1
C2	4.7μF/400V, electrolytic	1	R3	3.3MΩ/0.25W	1
C3	3.3μF/50V, electrolytic	1	R5	3.9Ω , 0805	1
C5	1nF/1kV, ceramic	1	R6	150kΩ, 1206	1
C8	0.01μF, 0805	1	R7	$1.3\Omega, 1206$	1
C11	1nF, 0805	1	R8	20kΩ, 0805	1
C12	470μF/10V	1	R9	$13k\Omega$, 0805	1
D1 to D6	1N4007, rectifier diode	2	R10	$200\Omega, 0805$	1
D12	APD260	6	R11	$27\Omega, 0805$	1
L1	470μH, inductor	1	R12	1.2kΩ, 0805	1
L2	Bead, 0805	1	T1	EE13 core, PC40, transformer	1
U1	AP3967	1			



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Mechanical Dimensions

SOIC-7 Unit: mm(inch)



Note: Eject hole, oriented hole and mold mark is optional.





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